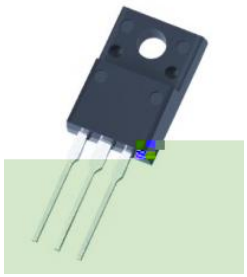
Silicon NPN transistor in a TO-220F Plastic Package.

Good linearity of h_{FE}, complementary to KTA1658.

General purpose amplifier.

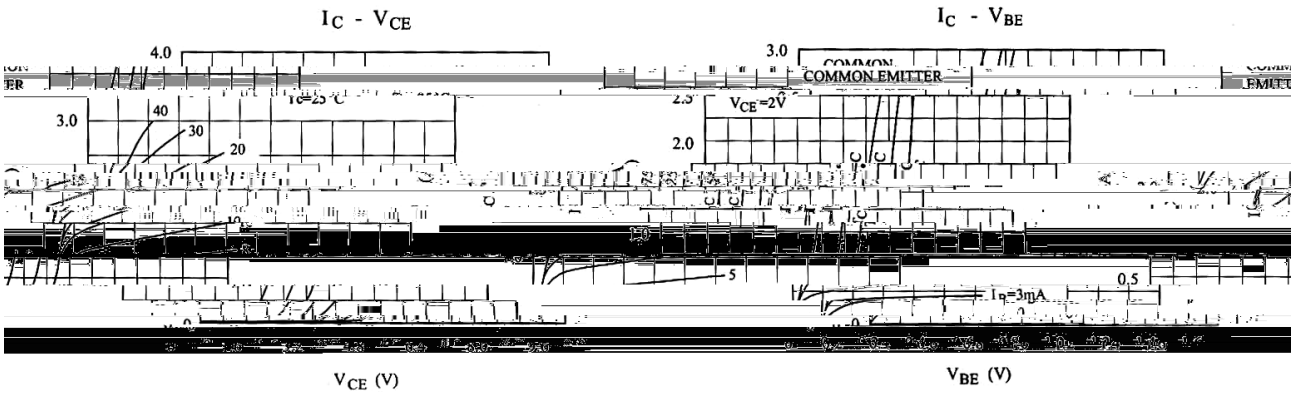


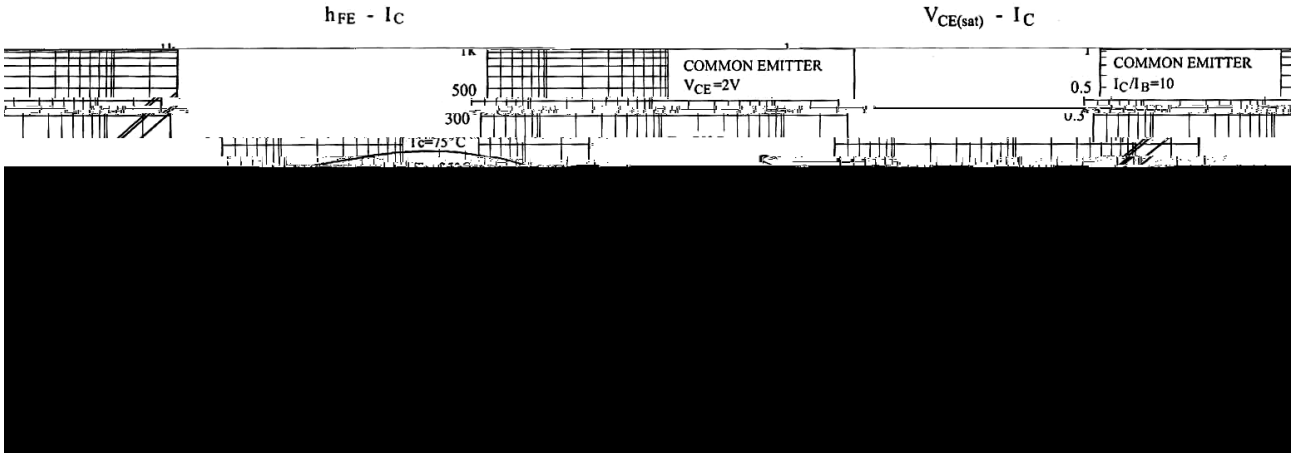
PIN1 Base PIN 2 Collector PIN 3 Emitter

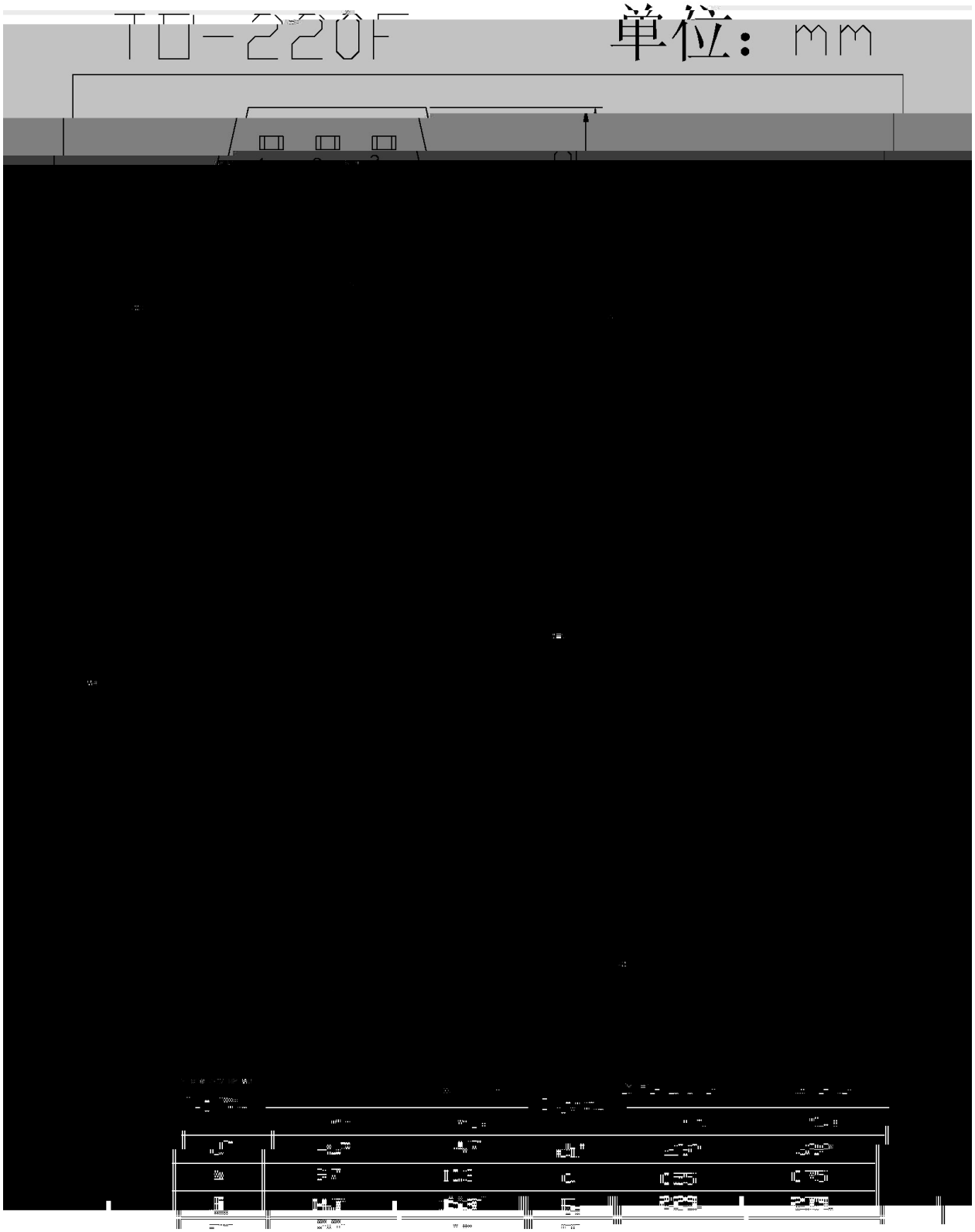
h_{FE} Classifications Symbol	O	Y

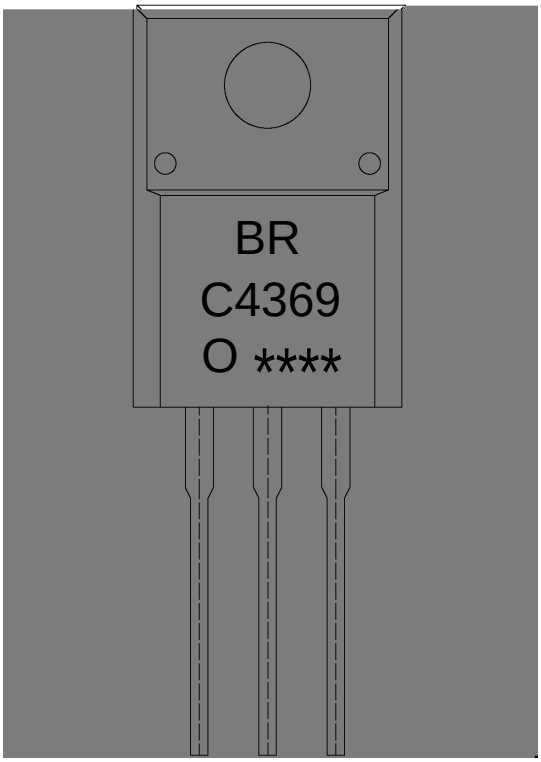
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	3.0	A
Base Current	I_B	0.3	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	P_C(Tc=25)	15	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	30			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=20V I_E=0			1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			1.0	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=2.0V I_C=0.5A	70		240	
	$h_{FE(2)}$	V_{CE}=2.0V I_C=2.5A	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2.0A I_B=0.2A		0.3	0.8	V
Base to Emitter Voltage	V_{BE}	V_{CE}=2.0V I_C=0.5A		0.75	1.0	V
Transition Frequency	f_T	V_{CE}=2.0V I_C=0.5A		100		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		3.5		pF


I_C - V_{CE}
4.0
3.0
40
30
20
V_{CE} (V)
I_C - V_{BE}
3.0
COMMON EMITTER
V_{CE}=2V
2.0
0.5
I_B=3mA
V_{BE} (V)


h_{FE} - I_C
500
300
COMMON EMITTER
V_{CE}=2V
$V_{CE(sat)}$ - I_C
0.5
COMMON EMITTER
I_C/I_B=10


TO-220F
单位：mm



BR

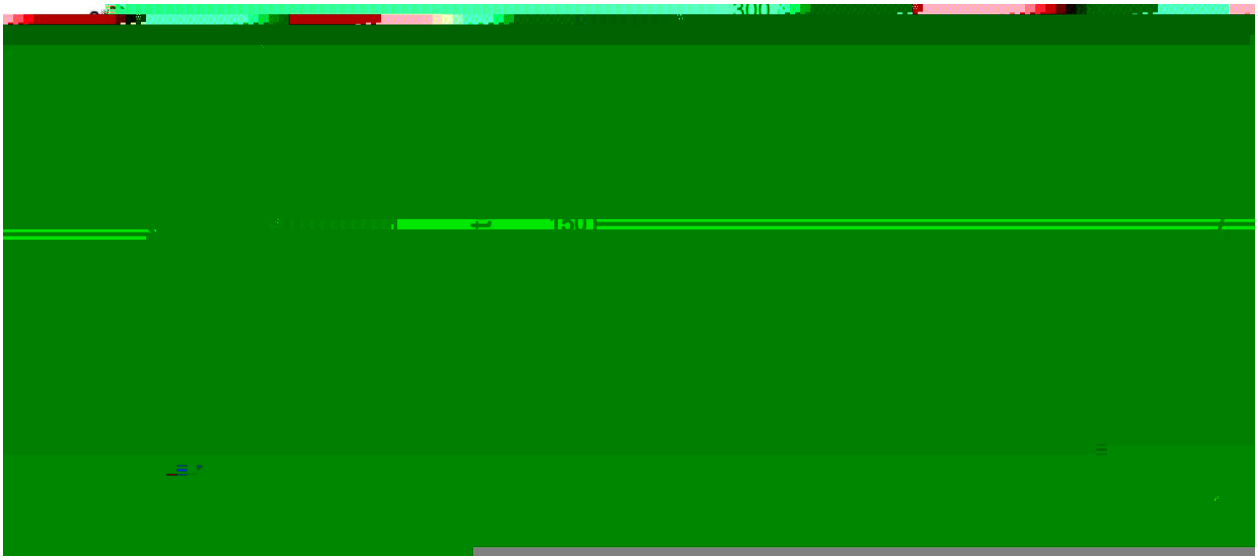
C4369

O: h_{FE}

****

Note:

BR:	Company Code.
C4369:	Product Type.
O:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.



	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.